

# Kazuyuki Suzuki

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Influences of microstructure on macroscopic crystallinity and magnetic properties of Sm-Fe-N fine powder produced by jet-milling. Journal of Alloys and Compounds, 2021, 869, 159288.	5.5	13
2	Cold welding behavior of fine bare aluminum powders prepared by new low oxygen induction thermal plasma system. Journal of Alloys and Compounds, 2018, 768, 608-612.	5.5	21
3	Improvement of magnetization of submicron-sized high coercivity Sm <sub>2</sub> Fe <sub>17</sub> N <sub>3</sub> powder by using hydrothermally synthesized sintering-tolerant cubic hematite. AIP Advances, 2017, 7, 056219.	1.3	10
4	Preparation of submicron-sized Sm <sub>2</sub> Fe <sub>17</sub> N <sub>3</sub> fine powder with high coercivity by reduction-diffusion process. Journal of Alloys and Compounds, 2017, 695, 1617-1623.	5.5	68
5	Preparation of highly dispersed core&ndash;shell $\alpha$ '-Fe <sub>16</sub> N <sub>2</sub> /SiO <sub>2</sub> particles using hydroxyapatite as a sintering prevention layer. Journal of the Ceramic Society of Japan, 2017, 125, 565-568.	1.1	1
6	Highly dispersive $\alpha$ -Fe <sub>16</sub> N <sub>2</sub> particle synthesis using hydroxyapatite coating. Journal of Solid State Chemistry, 2015, 225, 455-458.	2.9	6
7	Manipulation of Particles in a Microchannel with Various Geometric Spaces Using Ultrasound. Japanese Journal of Applied Physics, 2011, 50, 07HE27.	1.5	17
8	Organic Thin-Film Transistors with Tailored Liquid Sources of High- $\kappa$ HfO <sub>2</sub> Using Excimer Laser Irradiation. Japanese Journal of Applied Physics, 2011, 50, 01BC02.	1.5	1
9	Organic Thin-Film Transistors with Tailored Liquid Sources of High- $\kappa$ HfO <sub>2</sub> Using Excimer Laser Irradiation. Japanese Journal of Applied Physics, 2011, 50, 01BC02.	1.5	1
10	Dielectric Properties of HfO <sub>2</sub> Films Prepared on Flexible Polymer Substrates Using UV Irradiation. Key Engineering Materials, 2010, 445, 164-167.	0.4	1
11	Organic Thin-Film Transistors with Tailored Liquid Sources of HfO <sub>2</sub> as a High- $\kappa$ Insulator. Japanese Journal of Applied Physics, 2010, 49, 04DK08.	1.5	3
12	Characterization of high- $\kappa$ HfO <sub>2</sub> films prepared using chemically modified alkoxy-derived solutions. Journal of Applied Physics, 2009, 105, 061631.	2.5	13
13	Sol-Gel Synthesis of High- $\kappa$ HfO <sub>2</sub> Thin Films. Journal of the American Ceramic Society, 2009, 92, S162.	3.8	23
14	Surface morphology control of zirconia thin films prepared using novel photochromic molecules. Thin Solid Films, 2008, 516, 2635-2638.	1.8	8
15	Microstructure control of porous alumina film using aqueous sol containing poly(ethylene glycol). Journal of Electroceramics, 2008, 21, 524-527.	2.0	5
16	Patterning of HfO <sub>2</sub> Thin Films Using Chemical Solution and Dielectric Properties. Key Engineering Materials, 2008, 388, 141-144.	0.4	4
17	Fabrication of BaTiO <sub>3</sub> Thin Films Using Modified Chemical Solutions and Sintering Method. Japanese Journal of Applied Physics, 2008, 47, 7480-7485.	1.5	13
18	Effects of Flat HfO <sub>2</sub> Films Derived from Diethanolamine Solution on Structure and Properties of Metal/Ferroelectrics/Insulator/Semiconductor. Japanese Journal of Applied Physics, 2008, 47, 7561-7564.	1.5	2

#	ARTICLE	IF	CITATIONS
19	Structure and electrical characteristics of bottom-up BaTiO <sub>3</sub> films on Si. , 2008, , .		0
20	Preparation of ferroelectric (Y, Yb) MnO <sub>3</sub> films by chemical solution process. Journal of the Ceramic Society of Japan, 2008, 116, 265-270.	1.1	4
21	CHEMICAL SOLUTION DEPOSITION AND ELECTRICAL PROPERTIES OF (100)-PREDOMINANT BaTiO <sub>3</sub> THICKER FILMS. Integrated Ferroelectrics, 2007, 88, 51-57.	0.7	3
22	Morphology Control of Zirconia Thin Films Prepared Using Photochromic Precursors. Key Engineering Materials, 2007, 350, 133-136.	0.4	0
23	Effects of Modified Precursor Solution on Microstructure of (Y,Yb)MnO <sub>3</sub> /HfO <sub>2</sub> /Si. Japanese Journal of Applied Physics, 2007, 46, 6956-6959.	1.5	6
24	Photo-assisted crystallization of zirconia thin films prepared using chelate compounds. Journal of Materials Research, 2007, 22, 2608-2616.	2.6	3
25	Microstructure Control of Porous Alumina Film Using Aqueous Sol Containing Trehalose. Key Engineering Materials, 2007, 350, 7-10.	0.4	1
26	Improvement of Orientation and Characterization of Dielectric Property for (Y,Yb)MnO <sub>3</sub> /HfO <sub>2</sub> /Si Structures. Key Engineering Materials, 2007, 350, 107-110.	0.4	4
27	Construction of the (Y,Yb)MnO <sub>3</sub> /HfO <sub>2</sub> Stacking Layers through the Chemical Solution Process. Ferroelectrics, 2007, 357, 196-200.	0.6	0
28	Phase transition in bottom-up BaTiO <sub>3</sub> films on Si. Applied Physics Letters, 2007, 91, 172907.	3.3	16
29	CRYSTALLIZATION BEHAVIOR OF HfO <sub>2</sub> FILMS FOR (Y,Yb)MnO <sub>3</sub> /HfO <sub>2</sub> /Si STRUCTURES. Integrated Ferroelectrics, 2007, 94, 3-10.	0.7	6
30	Dielectric Properties of Alkoxy-Derived BaTiO <sub>3</sub> Films on LaNiO <sub>3</sub> /Pt/TiO <sub>x</sub> /Si(100). Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	0
31	Photo-assisted crystallization of zirconia thin films and their electrical evaluation. Thin Solid Films, 2007, 515, 4004-4010.	1.8	5
32	Structure and piezoelectric properties of 1- $\mu$ m-thick polar-axis-oriented CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> films. Applied Physics A: Materials Science and Processing, 2007, 87, 637-640.	2.3	3
33	Bottom-up fabrication and piezoelectric properties of CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> micro-plateaus. Applied Physics A: Materials Science and Processing, 2007, 88, 273-276.	2.3	0
34	Construction and characterization of alkoxy-derived (Y,Yb)MnO <sub>3</sub> /HfO <sub>2</sub> /Si structures for FeRAM application. Journal of Sol-Gel Science and Technology, 2007, 42, 251-256.	2.4	1
35	Composition Dependence of Microstructure and Dielectric Properties in Alkoxy-Derived Ba(Ti,Zr)O <sub>3</sub> Thin Films. Japanese Journal of Applied Physics, 2006, 45, 155-159.	1.5	9
36	Electrical properties of (100)-predominant BaTiO <sub>3</sub> films derived from alkoxy solutions of two concentrations. Acta Materialia, 2006, 54, 3893-3898.	7.9	29

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37	Downsizing of HfO <sub>2</sub> Layer for Pt/(Y,Yb)MnO <sub>3</sub> /HfO <sub>2</sub> /Si Structure. Japanese Journal of Applied Physics, 2006, 45, 7332-7335.	1.5	0
38	Thickness Dependence of Electrical Properties of Highly (100)-Oriented BaTiO <sub>3</sub> Thin Films Prepared by One-Step Chemical Solution Deposition. Japanese Journal of Applied Physics, 2006, 45, 855-859.	1.5	17
39	Effects of Hydrolysis on Photochromic ZrO <sub>2</sub> Precursor Solutions. Key Engineering Materials, 2006, 301, 87-90.	0.4	6
40	Characterization of Dielectric Properties of Alkoxy-Derived (Y,Yb)MnO <sub>3</sub> ; Ferroelectrics/Insulator Stacking Layers. Key Engineering Materials, 2006, 301, 65-70.	0.4	6
41	Characterization of Dielectric Properties of Alkoxy-Derived (Y,Yb)MnO <sub>3</sub> ; Ferroelectrics /HfO <sub>2</sub> ; Stacking Layers. Key Engineering Materials, 2006, 320, 73-76.	0.4	4
42	Synthesis of a New Photochromic ZrO <sub>2</sub> Precursor for Preparation of Functional Thin Films. Key Engineering Materials, 2006, 320, 175-178.	0.4	5
43	Dielectric and Piezoelectric Properties of Ba(Ti,Zr)O <sub>3</sub> Thin Films Consisted of Nano-Crystals. Key Engineering Materials, 2006, 301, 53-56.	0.4	3
44	Structure and Electrical Properties of Highly (100)-Oriented Ba(Zr <sub>0.05</sub> ;Ti <sub>0.95</sub> )O <sub>3</sub> ; Films Prepared by Chemical Solution Deposition. Advanced Materials Research, 2006, 11-12, 101-104.	0.3	1
45	Electrochemical Properties of Nanoporous TiO <sub>2</sub> Films. Key Engineering Materials, 2006, 301, 83-86.	0.4	1
46	Chemically Deposited (100)-Oriented BaTiO <sub>3</sub> Films with Highly Concentrated Solution Using High Crystallinity BaTiO <sub>3</sub> as a Buffer Layer. Key Engineering Materials, 2006, 320, 77-80.	0.4	1
47	Preparation and Characterization of Porous Alumina Film Using Sol Containing PEG. Key Engineering Materials, 2006, 320, 159-162.	0.4	1
48	IMPROVEMENT OF ALKOXY-DERIVED HfO <sub>2</sub> LAYERS FOR (Y, Yb)MnO <sub>3</sub> /HfO <sub>2</sub> /SI STRUCTURES. Integrated Ferroelectrics, 2006, 84, 121-127.	0.7	5
49	FERRO- AND PIEZOELECTRIC CHARACTERISTICS OF BOTTOM-UP FABRICATED CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> FILMS WITH PREFERRED ORIENTATION. Integrated Ferroelectrics, 2006, 80, 21-28.	0.7	0
50	Characterization of (Y,Yb)MnO <sub>3</sub> /Y <sub>2</sub> O <sub>3</sub> /Si Prepared from Alkoxide Solutions. Ferroelectrics, 2005, 329, 107-111.	0.6	1
51	Wavelength Dependence of Crystallization of Alkoxy-Derived ZrO <sub>2</sub> Thin Films Prepared by Ultraviolet Irradiation. Journal of Materials Research, 2005, 20, 3133-3140.	2.6	7
52	Dielectric and piezoelectric properties of highly (100)-oriented BaTiO <sub>3</sub> thin film grown on a Pt/TiO <sub>x</sub> /SiO <sub>2</sub> /Si substrate using LaNiO <sub>3</sub> as a buffer layer. Journal of Crystal Growth, 2005, 284, 190-196.	1.5	84
53	Crystal Phase and Orientation Control in Integrated Ferroelectric CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> Using a Tailored Liquid of Alkoxides. International Journal of Applied Ceramic Technology, 2005, 2, 64-72.	2.1	3
54	Effect of built-in bias fields on the nanoscale switching in ferroelectric thin films. Applied Physics A: Materials Science and Processing, 2005, 80, 1067-1070.	2.3	14

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55	Ferroelectric characteristics of silicate-bound Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> thin films. Applied Physics A: Materials Science and Processing, 2005, 80, 271-273.	2.3	0
56	Effect of amorphous TiO <sub>2</sub> buffer layer on the phase formation of CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> ferroelectric thin films. Applied Physics A: Materials Science and Processing, 2005, 81, 861-864.	2.3	5
57	Structure and ferro-/piezoelectric properties of bimorph-shape CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> films on Pt foils. Applied Physics A: Materials Science and Processing, 2005, 80, 1481-1484.	2.3	0
58	Ferro- and Piezoelectric Properties of CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> Films with Polar Axis Orientation. Integrated Ferroelectrics, 2005, 69, 143-149.	0.7	0
59	Impact of oxygen ambient on ferroelectric properties of polar-axis-oriented CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> films. Applied Physics Letters, 2005, 86, 112901.	3.3	19
60	INVESTIGATION OF ELECTRICAL PROPERTIES FOR (Y,Yb)MnO <sub>3</sub> /HfO <sub>2</sub> /Si and (Y,Yb)MnO <sub>3</sub> /Y <sub>2</sub> O <sub>3</sub> /Si STRUCTURES. Integrated Ferroelectrics, 2005, 75, 17-25.	0.7	8
61	Microstructure Control and Dielectric/Piezoelectric Properties of Alkoxy-Derived Ba(Ti,Zr)O <sub>3</sub> Thin Films. Japanese Journal of Applied Physics, 2005, 44, 6885-6890.	1.5	45
62	High piezoelectric response in polar-axis-oriented CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> ferroelectric thin films. Applied Physics Letters, 2004, 85, 3519-3521.	3.3	18
63	Frequency Dependence of Polarization Hysteresis Loop in CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>14</sub> Ferroelectric Thin Films. Integrated Ferroelectrics, 2004, 61, 19-23.	0.7	5
64	Ferro- and piezoelectric properties of polar-axis-oriented CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> films. Applied Physics Letters, 2004, 84, 3771-3773.	3.3	46
65	Polarization Switching in CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> Ferroelectric Thin Films. Key Engineering Materials, 2004, 269, 41-44.	0.4	2
66	Effects of $\hat{I}^2$ -diketone Addition on Crystallinity of Photo-Assisted Alkoxy-Derived Zirconia Thin Films. Key Engineering Materials, 2004, 269, 125-128.	0.4	6
67	Preparation of Nanoporous TiO <sub>2</sub> Film Using Aqueous Sol with Trehalose. Key Engineering Materials, 2004, 269, 87-90.	0.4	7
68	Construction of MFIS Structure Using Alkoxy-Derived (Y,Yb)MnO <sub>3</sub> Thin Films. Key Engineering Materials, 2004, 269, 49-52.	0.4	3
69	Composition Dependence of Lead-Free Ferroelectric Ba(Ti,Zr)O <sub>3</sub> Thin Films Fabricated by Chemical Solution Deposition Process. Key Engineering Materials, 2004, 269, 57-60.	0.4	6
70	Novel (Y,Yb)MnO <sub>3</sub> Thin Films for FeRAM Application. Integrated Ferroelectrics, 2004, 65, 117-123.	0.7	8
71	Fabrication and Characterization of Ba(Ti,Zr)O <sub>3</sub> Thin Films Through the Chemical Solution Deposition Process. Integrated Ferroelectrics, 2004, 64, 227-236.	0.7	9
72	Grain Size Effect on Dielectric and Piezoelectric Properties of Alkoxy-Derived BaTiO <sub>3</sub> -Based Thin Films. Japanese Journal of Applied Physics, 2004, 43, 6525-6529.	1.5	42

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73	Ferroelectric-Gate Field Effect Transistors Using (Y,Yb)MnO <sub>3</sub> /Y <sub>2</sub> O <sub>3</sub> /Si(111) Structures for 1T-Type FeRAMs. Integrated Ferroelectrics, 2004, 65, 169-174.	0.7	0
74	Current Status of Bi-Based Precursors for Integrated Ferroelectrics. Integrated Ferroelectrics, 2004, 62, 133-140.	0.7	5
75	Preparation of thick TiO <sub>2</sub> film with large surface area using aqueous sol with poly(ethylene glycol). Journal of Materials Science, 2004, 39, 699-701.	3.7	30
76	Preparation of nanoporous TiO <sub>2</sub> film with large surface area using aqueous sol with trehalose. Materials Letters, 2004, 58, 2751-2753.	2.6	38
77	Novel Ferroelectric Candidates in a Series of ABi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> (A: Alkaline Earth Metals) Thin Films. Integrated Ferroelectrics, 2003, 52, 3-10.	0.7	2
78	Ferroelectric Property of Alkoxy-Derived YMnO <sub>3</sub> Films Crystallized in Argon. Japanese Journal of Applied Physics, 2003, 42, 5692-5695.	1.5	17
79	Control of Crystallinity of Alkoxy-Derived Zirconia Thin Films by UV Irradiation. Key Engineering Materials, 2003, 248, 125-128.	0.4	3
80	Control of crystallization and crystal orientation of alkoxy-derived SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> thin films by ultraviolet irradiation. Journal of Materials Research, 2003, 18, 899-907.	2.6	17
81	Observation of Domain Structures in Bi-Based CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> Thin Films by Scanning Force Microscopy. Ferroelectrics, 2003, 291, 49-54.	0.6	4
82	Dynamics of nanoscale polarization backswitching in tetragonal lead zirconate titanate thin film. Applied Physics Letters, 2003, 82, 2130-2132.	3.3	38
83	Compositional Dependence of Ferroelectric Properties for (Y,Yb)MnO <sub>3</sub> Thin Films Prepared by Chemical Solution Deposition. Integrated Ferroelectrics, 2003, 52, 55-61.	0.7	6
84	Preparation of (Y,Yb)MnO <sub>3</sub> /Y <sub>2</sub> O <sub>3</sub> /Si (MFIS) Structure by Chemical Solution Deposition Method. Japanese Journal of Applied Physics, 2003, 42, 6007-6010.	1.5	19
85	Piezoelectric Properties of CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> Ferroelectric Thin Films Investigated by Atomic Force Microscopy. Japanese Journal of Applied Physics, 2003, 42, 5994-5997.	1.5	16
86	Ferroelectric Properties of (Y,Yb)MnO <sub>3</sub> Thin Films Prepared Using Alkoxide Solutions. Key Engineering Materials, 2003, 248, 77-82.	0.4	9
87	Synthesis of Ferroelectric YMnO <sub>3</sub> Thin Film by Chemical Solution Deposition. Key Engineering Materials, 2002, 214-215, 151-156.	0.4	10
88	Platinum-assisted phase transition in bismuth-based layer-structured ferroelectric CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> thin films. Applied Physics Letters, 2002, 81, 3227-3229.	3.3	31
89	Effects of Annealing Conditions on Crystallization of Hexagonal Manganite Films. Ferroelectrics, 2002, 270, 99-104.	0.6	10
90	Effects of Substrates on Alkoxy-Derived (Y,Yb)MnO <sub>3</sub> Thin Films. Integrated Ferroelectrics, 2002, 47, 91-100.	0.7	6

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91	Investigation of Domain Switching and Retention in Oriented PbZr <sub>0.3</sub> Ti <sub>0.7</sub> O <sub>3</sub> Thin Film by Scanning Force Microscopy. Japanese Journal of Applied Physics, 2002, 41, 6724-6729.	1.5	15
92	Chemical Approach Using Tailored Liquid Sources for Traditional and Novel Ferroelectric Thin Films. Japanese Journal of Applied Physics, 2002, 41, 6829-6835.	1.5	16
93	Local Piezoelectric Response in Bismuth-Based Ferroelectric Thin Films Investigated by Scanning Force Microscopy. Japanese Journal of Applied Physics, 2002, 41, L1103-L1105.	1.5	15
94	Effect of Polymer Addition on Microstructure of Porous TiO <sub>2</sub> Film. Key Engineering Materials, 2002, 228-229, 131-136.	0.4	2
95	Preparation and Characterization of Layer-Structured Perovskite Ca <sub>X</sub> Bi <sub>4-2X</sub> Ti <sub>3</sub> O <sub>12-X/2</sub> (X = 1, 2) Thin Films. Key Engineering Materials, 2002, 228-229, 93-98.	0.4	0
96	Effects of Composition on Crystallographic Properties of Alkoxy-Derived (Y,Yb)MnO <sub>3</sub> Thin Films. Key Engineering Materials, 2002, 228-229, 141-146.	0.4	2
97	Structure and Ferroelectric Properties of Alkoxy-Derived Ca <sub>2</sub> Bi <sub>4</sub> Ti <sub>5</sub> O <sub>18</sub> Thin Films on Pt(111)/TiO <sub>x</sub> /SiO <sub>2</sub> /Si(100). Japanese Journal of Applied Physics, 2002, 41, 2110-2114.	1.5	4
98	Photo-Assisted Control of Surface Morphology of Alkoxy-Derived ZrO <sub>2</sub> Thin Films. Key Engineering Materials, 2002, 228-229, 147-154.	0.4	5
99	Special Issue Ceramics Integration. Integration of Ferroelectric Ca <sub>2</sub> Bi <sub>4</sub> Ti <sub>5</sub> O <sub>18</sub> Thin Films on Pt-Passivated Si via Spin-Coating Technique.. Journal of the Ceramic Society of Japan, 2002, 110, 403-407.	1.3	0
100	Platinum-Accelerated Phase Transition in Bismuth-Based Layer-Structured Ferroelectric Thin Films. Materials Research Society Symposia Proceedings, 2002, 748, 1.	0.1	1
101	Novel chemical processing for crystallization of SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> thin films via UV irradiation. Materials Letters, 2002, 52, 20-23.	2.6	15
102	Preparation and orientation control of RMnO <sub>3</sub> (R=Y, Yb) thin film by chemical solution deposition. Journal of Crystal Growth, 2002, 237-239, 482-486.	1.5	12
103	Low-temperature synthesis in vacuum of c-axis oriented ferroelectric YMnO <sub>3</sub> thin films using alkoxy-derived precursors. Integrated Ferroelectrics, 2001, 40, 155-162.	0.7	2
104	Chemical processing and characterization of ferroelectric thin films of bismuth-based layer-structured perovskite CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> with the octahedron number of 4. Integrated Ferroelectrics, 2001, 36, 321-329.	0.7	0
105	Ferroelectric properties of alkoxy-derived lanthanum-modified bismuth titanate thin films. Integrated Ferroelectrics, 2001, 36, 173-181.	0.7	10
106	Synthesis of YMnO <sub>3</sub> thin films from alkoxy-derived precursors. Ferroelectrics, 2001, 263, 285-290.	0.6	2
107	Control of Crystal Structure of SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> Thin Films by UV Irradiation. Key Engineering Materials, 2001, 214-215, 145-150.	0.4	1
108	Preparation and Ferroelectric Properties of CaBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> /BaBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> Thin Films on Pt-Passivated Silicon. Key Engineering Materials, 2001, 214-215, 139-144.	0.4	0

#	ARTICLE	IF	CITATIONS
109	Comparison of Microstructure and Ferroelectric Properties of Alkoxy-Derived $\text{MBi}_4\text{Ti}_4\text{O}_{15}$ (M: Ca or Tj) $\text{ETQq1}$ $1.0.784314$ $\text{rgBT} / \text{Overl}$	1.5	22
110	Ferroelectric properties of alkoxy-derived $\text{CaBi}_4\text{Ti}_4\text{O}_{15}$ thin films on Pt-passivated Si. Applied Physics Letters, 2001, 78, 1119-1121.	3.3	71
111	Effects of $\text{BaBi}_2\text{Ta}_2\text{O}_9$ thin buffer layer on crystallization and electrical properties of $\text{CaBi}_2\text{Ta}_2\text{O}_9$ thin films on Pt-coated silicon. Journal of Applied Physics, 2001, 89, 5088-5092.	2.5	3
112	Phase transition, ferroelectric, and dielectric properties of layer-structured perovskite $\text{CaBi}_3\text{Ti}_3\text{O}_{12}$ thin films. Applied Physics Letters, 2001, 79, 397-399.	3.3	5
113	Ferroelectric and Fatigue Properties of Alkoxy-Derived $\text{CaBi}_2\text{Ta}_2\text{O}_9$ Thin Films. Materials Research Society Symposia Proceedings, 2000, 655, 126.	0.1	1
114	Preparation of Layer-Structured $\text{CaBi}_2\text{Ta}_2\text{O}_9$ Ferroelectric Thin Films through a Triple Alkoxide Route. Japanese Journal of Applied Physics, 2000, 39, 5501-5504.	1.5	11
115	Ferroelectric properties of alkoxy-derived $\text{CaBi}_2\text{Ta}_2\text{O}_9$ thin films. Journal of Applied Physics, 2000, 88, 3779-3780.	2.5	22
116	Dielectric and Pyroelectric Properties of Alkoxy-Derived $\text{KTa}_{0.35}\text{Nb}_{0.65}\text{O}_3$ Thin Film. Japanese Journal of Applied Physics, 1999, 38, 5953-5957.	1.5	4
117	UV Processing of Oriented $\text{KTa}_{0.50}\text{Nb}_{0.50}\text{O}_3$ Thin Films.. Journal of the Ceramic Society of Japan, 1999, 107, 1032-1036.	1.3	7
118	Processing of Oriented $\text{K}(\text{Ta},\text{Nb})\text{O}_3$ Films Using Chemical Solution Deposition. Journal of the American Ceramic Society, 1999, 82, 1463-1466.	3.8	31
119	Effect of Gel-Films-Thickness and Sintering Conditions on the Crystal Structure and Microstructure of Alkoxy-Derived $\text{BaTiO}_3$ Thin Films. Key Engineering Materials, 0, 388, 171-174.	0.4	0
120	Effects of UV Irradiation on Microstructure and Properties of $\text{HfO}_2$ Films Prepared from Alkoxy-Derived Precursor Solution. Key Engineering Materials, 0, 421-422, 91-94.	0.4	1
121	Polar Axis Orientation and Electrical Properties of Alkoxy-Derived One Micro-Meter-Thick Ferro-/Piezoelectric Films. , 0, , 33-42.		0